

### **Description**

The HXY3401MI uses advanced trench technology

to provide excellent R<sub>DS(ON)</sub>, low gate charge and

operation with gate voltages as low as 2.5V. This

device is suitable for use as a

Battery protection or in other Switching application.

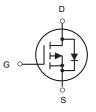


#### **General Features**

 $V_{DS} = -30V I_{D} = -4.2A$ 

 $R_{DS(ON)} < 54m\Omega$ @  $V_{GS}=10V$ 

 $R_{DS(ON)} < 77 m\Omega@V_{GS}=4.5V$ 



## **Application**

Battery protection

Load switch

Uninterruptible power supply

P-Channel MOSFET

### **Package Marking and Ordering Information**

Product ID	Pack	Marking	Qty(PCS)
HXY3401MI	SOT23-3L	X1KX	3000

### Absolute Maximum Ratings (T<sub>A</sub>=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V <sub>D</sub> s	Drain-Source Voltage	-30	V
V <sub>G</sub> s	Gate-Source Voltage	±12	V
I <sub>D</sub>	Drain Current-Continuous	-4.2	A
Ірм	Drain Current-Pulsed (Note 1)	-30	A
P <sub>D</sub>	Maximum Power Dissipation	1.2	W
T <sub>J</sub> ,T <sub>STG</sub>	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}$
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	104	°C/W



Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS}$ =-24 $V$ , $V_{GS}$ =0 $V$	-	-	-1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±10V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						•
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =-250μA	-0.7	-1	-1.3	V
		V <sub>GS</sub> =-10V, I <sub>D</sub> =-4.2A	-	46	54	mΩ
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4A	-	58	77	mΩ
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-1A		74	130	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =-5V,I <sub>D</sub> =-4.2A	-	10	-	S
Dynamic Characteristics (Note4)					•	•
Input Capacitance	C <sub>lss</sub>	V <sub>DS</sub> =-15V,V <sub>GS</sub> =0V,	-	880	-	PF
Output Capacitance	C <sub>oss</sub>		-	105	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0MHz	-	65	-	PF
Switching Characteristics (Note 4)						•
Turn-on Delay Time	t <sub>d(on)</sub>		-	7	-	nS
Turn-on Rise Time	t <sub>r</sub>	V <sub>DD</sub> =-15V,I <sub>D</sub> =-4.2A	-	3	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =-10V, $R_{GEN}$ =6 $\Omega$	-	30	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	12	-	nS
Total Gate Charge	Qg	V <sub>DS</sub> =-15V,I <sub>D</sub> =-4.2A,V <sub>GS</sub> =-4.5V	-	8.5	-	nC
Gate-Source Charge	$Q_{gs}$		-	1.8	-	nC
Gate-Drain Charge	$Q_{gd}$		-	2.7	-	nC
Drain-Source Diode Characteristics						•
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =-4.2A	-	-	-1.2	V
	•	•		•		

#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width  $\leq$  300 $\mu$ s, Duty Cycle  $\leq$  2%.
- 4. Guaranteed by design, not subject to production



## Typical Electrical and Thermal Characteristics

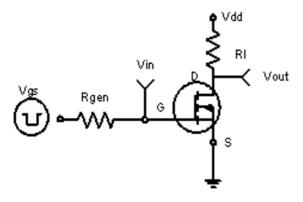
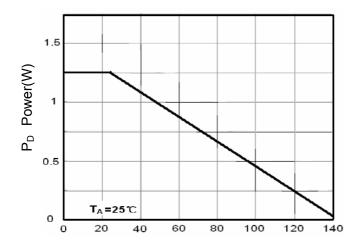
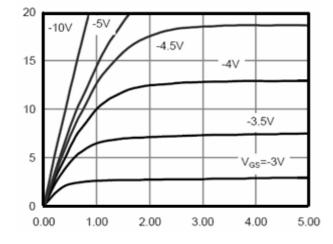


Figure 1:Switching Test Circuit



 $T_J$ -Junction Temperature ( ${}^{\circ}$ C) Figure 3 Power Dissipation



Ip- Drain Current (A)

Vds Drain-Source Voltage (V) Figure 5 Output Characteristics

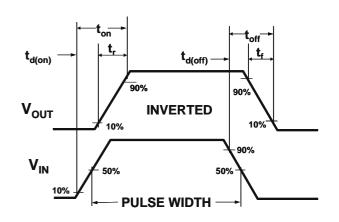


Figure 2:Switching Waveforms

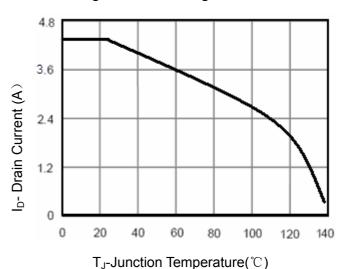


Figure 4 Drain Current

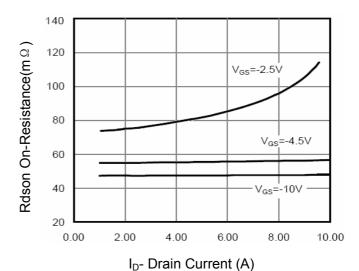
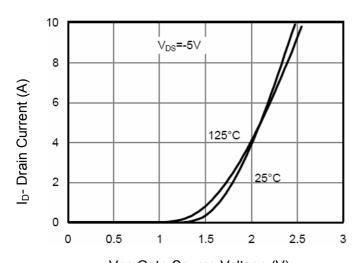
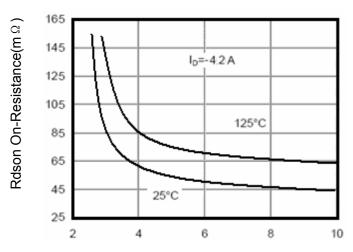


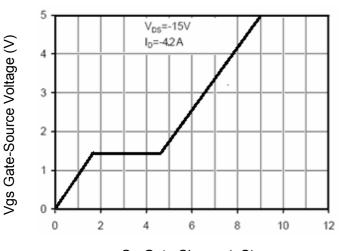
Figure 6 Drain-Source On-Resistance



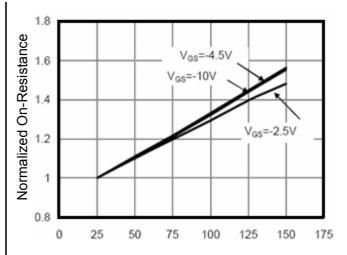
Vgs Gate-Source Voltage (V) Figure 7 Transfer Characteristics



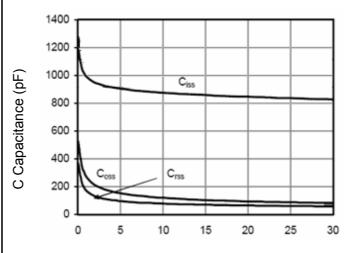
Vgs Gate-Source Voltage (V) Figure 9 Rdson vs Vgs



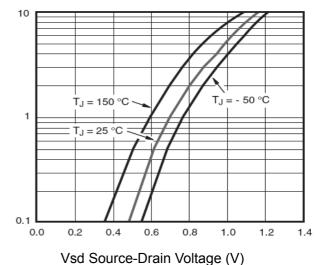
Qg Gate Charge (nC) Figure 11 Gate Charge



 $\label{eq:TJ-Junction} T_{J}\mbox{-Junction Temperature}({}^{\circ}\!\mathbb{C})$  Figure 8 Drain-Source On-Resistance



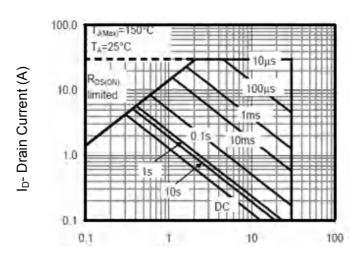
Vds Drain-Source Voltage (V) Figure 10 Capacitance vs Vds



Is- Reverse Drain Current (A)

Figure 12 Source- Drain Diode Forward





Vds Drain-Source Voltage (V)
Figure 13 Safe Operation Area

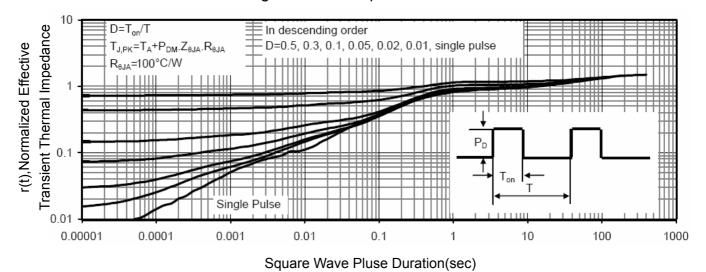
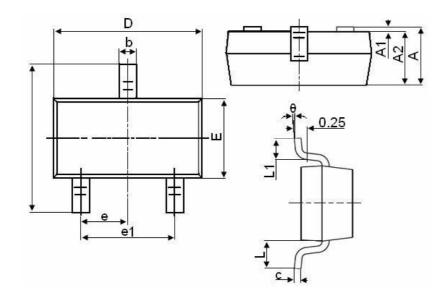


Figure 14 Normalized Maximum Transient Thermal Impedance



# **SOT23-3L Package Information**



Symbol	Dimensions in Millimeters			
	MIN.	MAX.		
А	1.050	1.250		
A1	0.000	0.100		
A2	1.050	1.150		
b	0.300	0.500		
С	0.100	0.200		
D	2.800	3.000		
E	1.500	1.700		
E1	2.650	2.950		
е		0.950TYP		
e1	1.800	2.000		
L		0.550REF		
L1	0.300	0.600		
θ	0°	8°		



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